

# Yoshiki Saito

## List of Publications by Year in descending order

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28  
papers

2,005  
citations

686830

13  
h-index

610482

24  
g-index

28  
all docs

28  
docs citations

28  
times ranked

1498  
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural design optimization of 279 nm wavelength AlGaIn homojunction tunnel junction deep-UV light-emitting diode. Applied Physics Express, 2022, 15, 044003.	1.1	6
2	Reduction in operating voltage of AlGaIn homojunction tunnel junction deep-UV light-emitting diodes by controlling impurity concentrations. Applied Physics Express, 2021, 14, 084001.	1.1	17
3	Efficiency improvement of AlGaIn-based deep-ultraviolet light-emitting diodes and their virus inactivation application. Japanese Journal of Applied Physics, 2021, 60, 080501.	0.8	20
4	Formation mechanism and suppression of Ga-rich streaks at macro-step edges in the growth of AlGaIn on an AlN/sapphire-template. Journal of Crystal Growth, 2020, 534, 125475.	0.7	6
5	Low resistivity of highly Si-doped n-type Al <sub>0.62</sub> Ga <sub>0.38</sub> N layer by suppressing self-compensation. Applied Physics Express, 2020, 13, 025504.	1.1	28
6	Electronic degeneracy conduction in highly Si-doped Al <sub>0.6</sub> Ga <sub>0.4</sub> N layers based on the carrier compensation effect. Applied Physics Letters, 2020, 117, .	1.5	16
7	Origin of optical absorption in AlN with air voids. Japanese Journal of Applied Physics, 2019, 58, SC329.	0.8	11
8	Sapphire substrate off-angle and off-direction dependences on characteristics of AlGaIn-based deep ultraviolet light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1025.	0.8	12
9	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2004, 241, 3107-3112.	0.7	5
10	Recent development of InN RF-MBE growth and its structural and property characterization. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1487-1495.	0.8	16
11	MBE-growth, characterization and properties of InN and InGaIn. Physica Status Solidi A, 2003, 200, 202-208.	1.7	45
12	Effect of AlN buffer layer on the growth of InN epitaxial film on Si substrate. Physica Status Solidi (B): Basic Research, 2003, 240, 429-432.	0.7	19
13	Influence of substrate polarity on growth of InN films by RF-MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2810-2813.	0.8	19
14	Band-Gap Energy and Physical Properties of InN Grown by RF-Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2003, 798, 259.	0.1	8
15	Single Crystalline InN Films Grown on Si Substrates By Using A Brief Substrate Nitridation Process. Materials Research Society Symposia Proceedings, 2002, 743, L3.26.1.	0.1	6
16	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	1.5	1,380
17	Optical Properties of In <sub>x</sub> Ga <sub>1-x</sub> N with Entire Alloy Composition on InN Buffer Layer Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 750-754.	0.7	65
18	Growth Temperature Dependence of Indium Nitride Crystalline Quality Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 796-800.	0.7	105

#	ARTICLE	IF	CITATIONS
19	Effect of atomic hydrogen irradiation on native oxides of InN surface. Journal of Crystal Growth, 2002, 237-239, 1022-1026.	0.7	13
20	Two Step Growth of InN Films on Sapphire (0001) Substrates Without Nitridation Process by RF-MBE. Materials Research Society Symposia Proceedings, 2001, 693, 477.	0.1	0
21	Polarity of High-Quality Indium Nitride Grown by RF Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 13-16.	0.7	17
22	Study of Epitaxial Relationship in InN Growth on Sapphire (0001) by RF-MBE. Physica Status Solidi (B): Basic Research, 2001, 228, 17-20.	0.7	5
23	Growth of AlN films on SiC substrates by RF-MBE and RF-MEE. Journal of Crystal Growth, 2001, 230, 392-397.	0.7	34
24	Growth of High-Electron-Mobility InN by RF Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, L91-L93.	0.8	91
25	Electrical Properties of InN Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2000, 639, 11181.	0.1	4
26	<i>m</i> -Plane GaInN Light Emitting Diodes Grown on Patterned <i>a</i> -Plane Sapphire Substrates. Applied Physics Express, 0, 2, 041001.	1.1	28
27	<i>a</i> -Plane GaN Films Grown on Patterned <i>a</i> -Plane Sapphire Substrates with 3-inch Diameter. Applied Physics Express, 0, 2, 031002.	1.1	26
28	Visualization of depletion layer in AlGaIn homojunction p-n junction. Applied Physics Express, 0, , .	1.1	3